



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD FOR GROWING A GATE OXIDE LAYER ON A SILICON SURFACE WITH PRELIMINARY N2O ANNEAL		
Application Type :		regular, utility	
Attorney Docket Number :		NTCP0014USA	
Correspondence address:			
Customer Number:		027765	
Priority Data:			
Doc.No: 093107164; Country -TW ; Date: 2004-03-17 us-priority-claimed			
Inventor Information:			
<u>Inventor 1:</u>			
Applicant Authority Type:		Inventor	
Citizenship:		TW	
Given Name:		Shian-Jyh	
Family Name:		Lin	
Residence:			
City of Residence:		Chia-Yi Hsien	
Country of Residence:		TW	
Address-1 of Mailing Address:		No. 18, Community 1, Ta-Ping-Ting, Yi-Lung Tsun,	
Address-2 of Mailing Address:		Chu-Chi Hsiang	
City of Mailing Address:		Chia-Yi Hsien	
State of Mailing Address:			
Postal Code of Mailing Address:			
Country of Mailing Address:		TW	
Phone:			
Fax:			
E-mail:			
Attorney Information:			
practitioner(s) at Customer Number:			
027765			

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